

Performance and traps of Ga₂O₃ Schottky barrier diodes with mesa structure

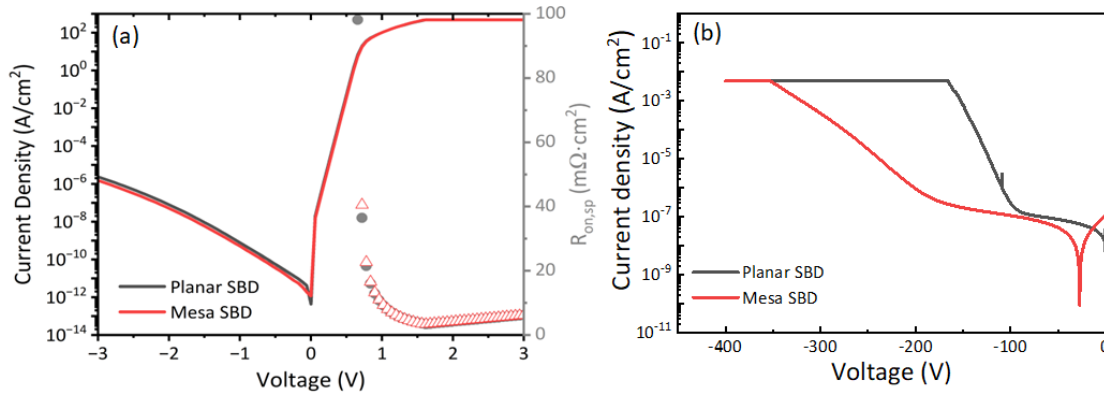


Fig. 1. (a) Current-voltage characteristics of Ga₂O₃ SBD with general and mesa structure. (b) Reverse biased current characteristics of SBDs.

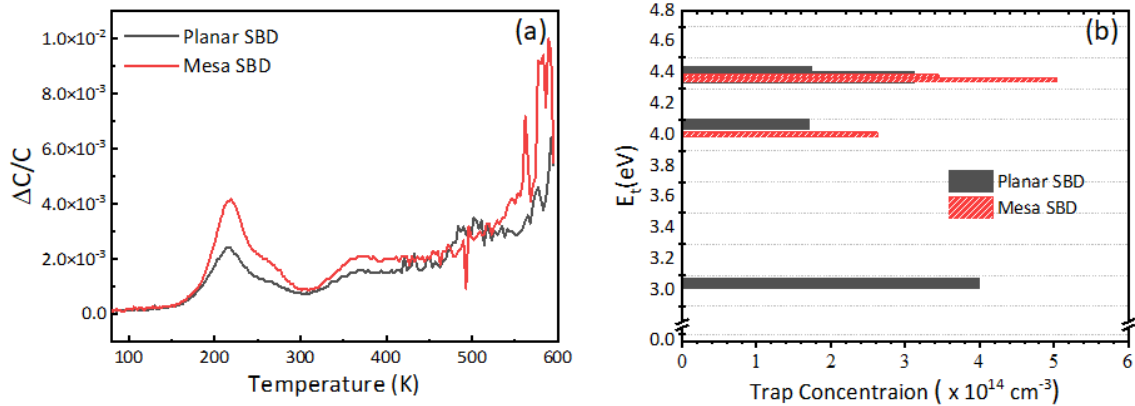


Fig. 2. (a) DLTS spectra of Planar and Mesa SBD. (b) Summary of the trap energy of SBDs from result (a).

References

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- [2] Identification and Suppression of Majority Surface States in the Dry-Etched β -Ga₂O₃. *J. Phys. Chem. Lett.* 2022, 13, 7094–7099